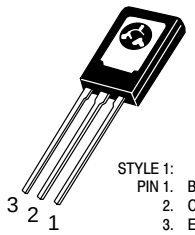
Complementary Silicon Power Transistors

. . . designed specifically for use with the MC3419 Solid–State Subscriber Loop Interface Circuit (SLIC).

- High Safe Operating Area
  $I_{S/B}$ @ 40 V, 1.0 s = 0.375 A — TO–126
- Collector–Emitter Sustaining Voltage
  $V_{CEO(sus)}$ = 100 Vdc (Min)
- High DC Current Gain
  h_{FE} @ 120 mA, 10 V = 1500 (Min)

NPN
MJE270
PNP
MJE271

2.0 AMPERE
COMPLEMENTARY
POWER DARLINGTON
TRANSISTORS
100 VOLTS
15 WATTS



CASE 77–09
TO–225AA TYPE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	100	Vdc
Collector–Base Voltage	V_{CB}	100	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current — Continuous — Peak	I_C	2.0 4.0	Adc
Base Current	I_B	0.1	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 0.12	Watts W/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.5 0.012	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.33	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	100	—	Vdc
Collector Cutoff Current (V_{CE} = 100 Vdc, I_B = 0)	I_{CEO}	—	1.0	mAdc
Collector Cutoff Current (V_{CB} = 100 Vdc, I_E = 0)	I_{CBO}	—	0.3	mAdc
Emitter Cutoff Current (V_{BE} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	0.1	mAdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 40 Vdc, t = 1.0 s, non–repetitive)	$I_{S/b}$	375	—	Adc
ON CHARACTERISTICS (1)				
DC Current Gain (I_C = 20 mAdc, V_{CE} = 3.0 Vdc) (I_C = 120 mAdc, V_{CE} = 10 Vdc)	h_{FE}	 500 1500	 — —	—
Collector–Emitter Saturation Voltage (I_C = 20 mAdc, I_B = 0.2 mAdc) (I_C = 120 mAdc, I_B = 1.2 mAdc)	$V_{CE(sat)}$	 — —	 2.0 3.0	Vdc
Base–Emitter On Voltage (I_C = 120 mAdc, V_{CE} = 10 Vdc)	$V_{BE(on)}$	—	2.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain — Bandwidth Product (2) (I_C = 0.05 Adc, V_{CE} = 5.0 Vdc, f_{test} = 1.0 MHz)	f_T	6.0	—	MHz

NOTES:
(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%
(2) $f_T = |h_{fe}| \bullet f_{test}$.

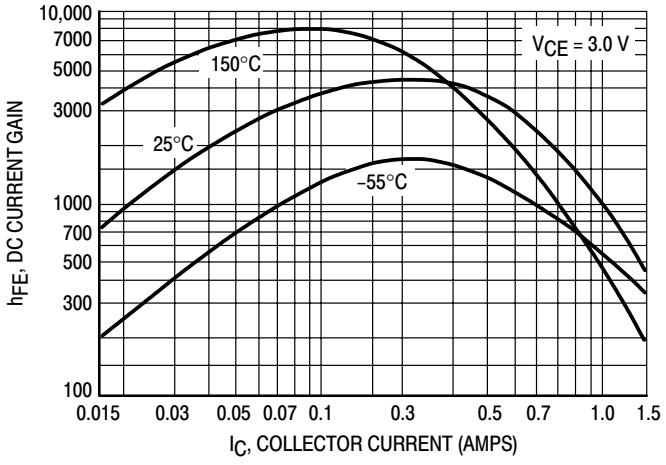


Figure 1. DC Current Gain

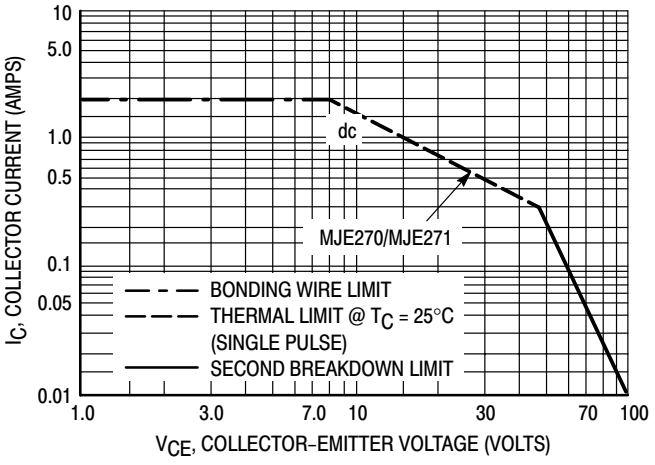
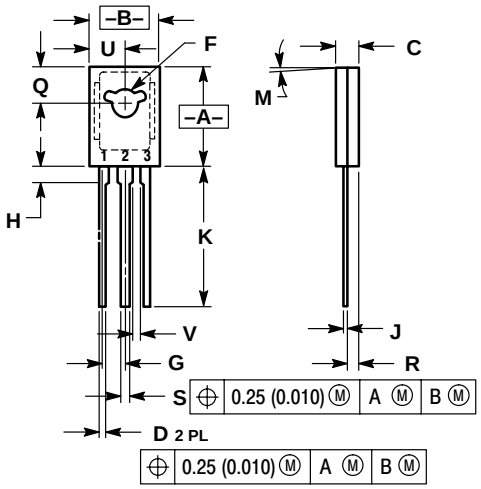


Figure 2. Safe Operating Area

PACKAGE DIMENSIONS

TO−225AA
CASE 77−09
ISSUE W



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

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